

n-oxyg. silicon sensor, 300  $\mu\text{m}$ ,  $1.45\text{e}12/\text{cm}^3$ ,  $V_{\text{bias}}=1.5\text{ V}$ ,  $V_{\text{dep}}=10\text{ ke}$ ,  $Q_{\text{in}}=10\text{ ke}$  @ 50  $\mu\text{m}$

differend quantities, see legend

